

**Control Chip, Parallel Input Gain/Phase Control  
8.0-11.0 GHz**

**MA03503D**  
Rev A  
Preliminary Information

**Features**

- ◆ 6-bit Phase Shifter and 5-bit Attenuator
- ◆ Parallel Control Input
- ◆ 50 Ω Input and Output Impedance
- ◆ GaAs MSAG<sup>®</sup> Process
- ◆ Proven Manufacturability and Reliability
  - No Airbridges
  - Polyimide Scratch Protection
  - No Hydrogen Poisoning Susceptibility

**Description**

The MA03503D is a parallel control input phase shifter/attenuator/buffer amplifier MMIC. The on-chip driver circuitry allows for control of the 6 phase and 5 attenuation bits using TTL/CMOS compatible voltage levels, and eliminates the need for complementary inputs. This product is fully matched to 50 ohms on both the input and output.

Fabricated using M/A-COM's repeatable, high performance and highly reliable GaAs Multifunction Self-Aligned Gate (MSAG<sup>®</sup>) Process, each device is 100% RF tested on wafer to ensure performance compliance.

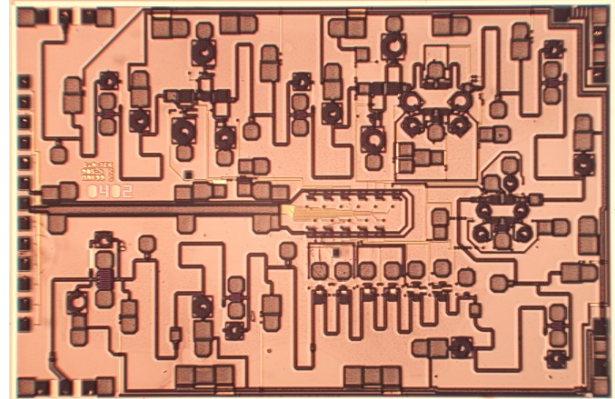
M/A-COM's MSAG process features robust silicon-like manufacturing processes, planar processing of ion implanted transistors, multiple implant capability enabling power, low-noise, switch and digital FETs on a single chip, and polyimide scratch protection for ease of use with automated manufacturing processes. The use of refractory metals and the absence of platinum in the gate metal formulation prevents hydrogen poisoning when employed in hermetic packaging.

**Electrical Characteristics:  $T_B = 25^{\circ}\text{C}^1$ ,  $Z_0 = 50\Omega$ ,  $V_{DD} = 5\text{V}$ ,  $V_{GG} = -4\text{V}$ ,  $V_{EE} = -4.0$**

Parameter	Symbol	Minimum	Typical	Maximum	Units
Bandwidth	f	8.0		11.0	GHz
Gain	Gn	13	18	22.5	dB
1-dB Compression Point	P1dB		22		dBm
Input Return Loss	IRL	10	16		dB
Output Return Loss	ORL	10	16		dB
Attenuation Range (5-bits, 0.75dB step)			23		dB
RMS Attenuation Error (Uncorrected)			0.2		dB
0.75 dB Attenuator Bit		0.5	0.8	1.0	dB
1.5 dB Attenuator Bit		1.0	1.5	2.0	dB
3 dB Attenuator Bit		2.4	3.0	3.6	dB
6 dB Attenuator Bit		5.0	6.0	7.0	dB
12 dB Attenuator Bit		10.8	12	13.2	dB

1.  $T_B$  = MMIC Base Temperature

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**Primary Applications**

- ◆ Radar Systems

- **North America** Tel: 800.366.2266 / Fax: 978.366.2266
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- **Asia/Pacific** Tel: 81.44.844.8296 / Fax: 81.44.844.8298

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Parameter	Symbol	Minimum	Typical	Maximum	Units
Phase Shift Range (6 bits, 5.6 degree step)			360		Deg
RMS Phase Error (Uncorrected)			2		Deg
5.6 Degree Bit		4.0	5.3	7.0	Deg
11.25 Degree Bit		8.0	11.0	13.0	Deg
22.5 Degree Bit		19.0	22.0	24.0	Deg
45 Degree Bit		40.0	44.0	47.0	Deg
90 Degree Bit		85.0	90.0	95.0	Deg
180 Degree Bit		170	180	190	Deg
Gain Variation over all Phase Shifter settings			+/-1.0		dB
Output Third Order Intercept Point	OTOI		28		dBm
Noise Figure	NF		10		dB
Drain Supply Current	$I_{DD}$	160	325	500	mA
Gate Supply Current	$I_{GG}$		1	10	mA
Digital Power Supply Current	$I_{EE}$		15	25	mA
Input Logic High Current			0.5		mA
Input Logic Low Current			0.1		mA
Timing Delay-Enable Signal to Bit Change			25		nS

**Absolute Maximum Conditions <sup>2</sup>**

Parameter	Symbol	Absolute Maximum	Units
Input Power	$P_{IN}$	20	dBm
Drain Supply Voltage	$V_{DD}$	8.0	V
Gate Supply Voltage	$V_{GG}$	-6.0	V
Quiescent Drain Current (No RF)	$I_{DQ}$	500	mA
Quiescent DC Power Dissipated (No RF)	$P_{DISS}$	2.5	W
Digital Power Supply Voltage	$V_{EE}$	-6.0	V
Junction Temperature	$T_J$	180	$^\circ\text{C}$
Storage Temperature	$T_{STG}$	-55 to +150	$^\circ\text{C}$
Die Attach Temperature		310	$^\circ\text{C}$

**2. Operation beyond these limits may result in permanent damage to the part.**

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### Recommended Operating Conditions <sup>3</sup>

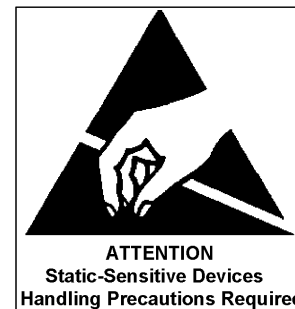
Characteristic	Symbol	Min	Typ	Max	Unit
Drain Supply Voltage	$V_{DD}$	4.0	5.0	6.0	V
Gate Supply Voltage	$V_{GG}$	-4.5	-4.0	-3.5	V
Digital Power Supply Voltage	$V_{EE}$	-4.2	-4.0	-3.8	V
Input Logic High Voltage	$V_{IH}$	3.0	3.5	5.0	V
Input Logic Low Voltage	$V_{IL}$	0.0	0.0	0.8	V
Clock Frequency	$F_{CLK}$		20		MHz
Junction Temperature	$T_J$			150	°C
MMIC Base Temperature	$T_B$			Note 4	°C

3. Operation outside of these ranges may reduce product reliability.  
4. Maximum MMIC Base Temperature =  $150^{\circ}\text{C} - 31.8^{\circ} * V_{DD} * I_{DQ}$

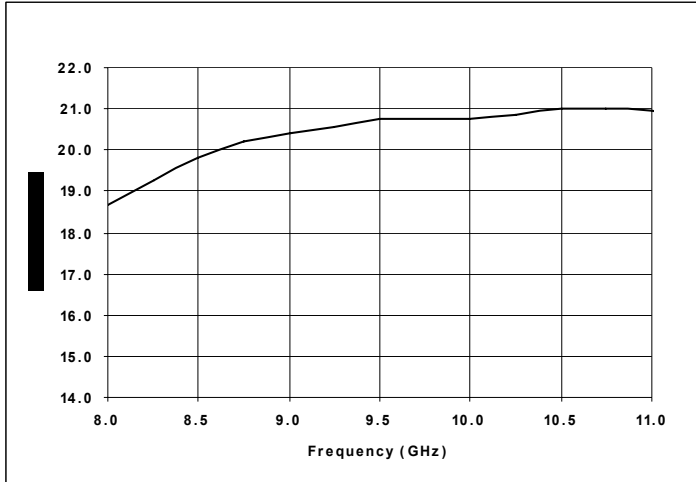
### Operating Instructions

This device is static sensitive. Please handle with care. To operate the device, follow these steps.

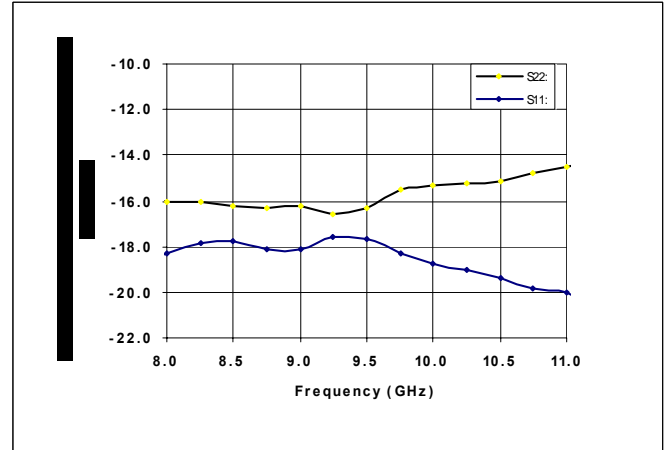
1. Apply  $V_{GG} = -4\text{ V}$ ,  $V_{EE} = -4\text{ V}$ ,  $V_{DD} = 0\text{ V}$ .
2. Ramp  $V_{DD}$  to desired voltage, typically 5 V.
3. Adjust  $V_{GG}$  to set  $I_{DQ}$ .
4. Set RF input.
5. Power down in reverse. Turn  $V_{GG}$  off last.



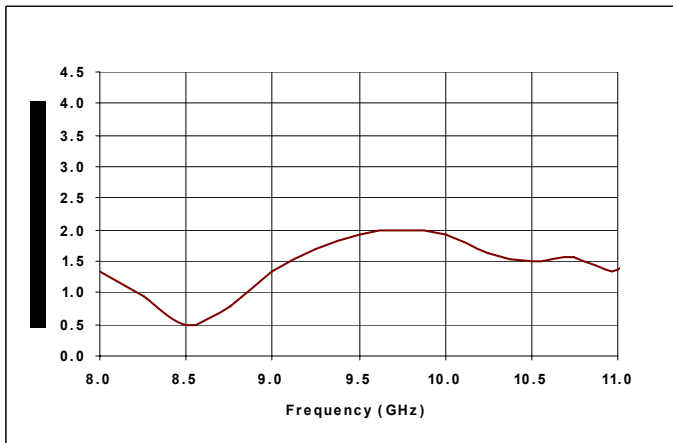
**Typical Small Signal Characteristics ( $V_{DD}=5V$ ,  $V_{GG}=-4V$ )**



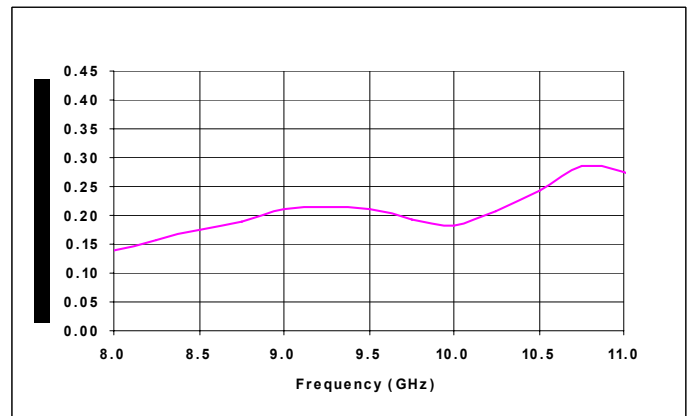
**Figure 1. Gain**



**Figure 2. Input and Output Match**



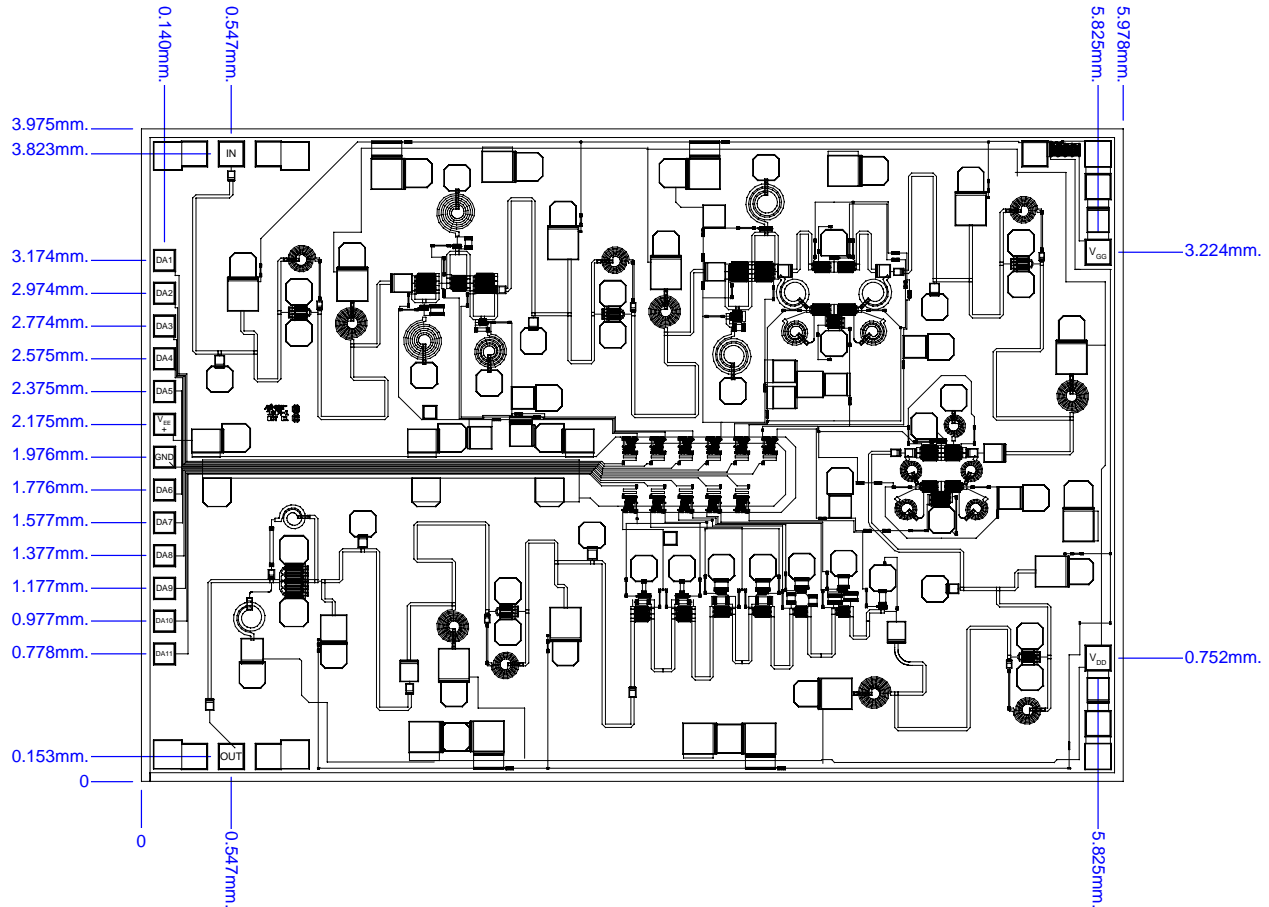
**Figure 3. RMS Attenuation Error**



**Figure 4. RMS Phase Error**

**Mechanical Information**

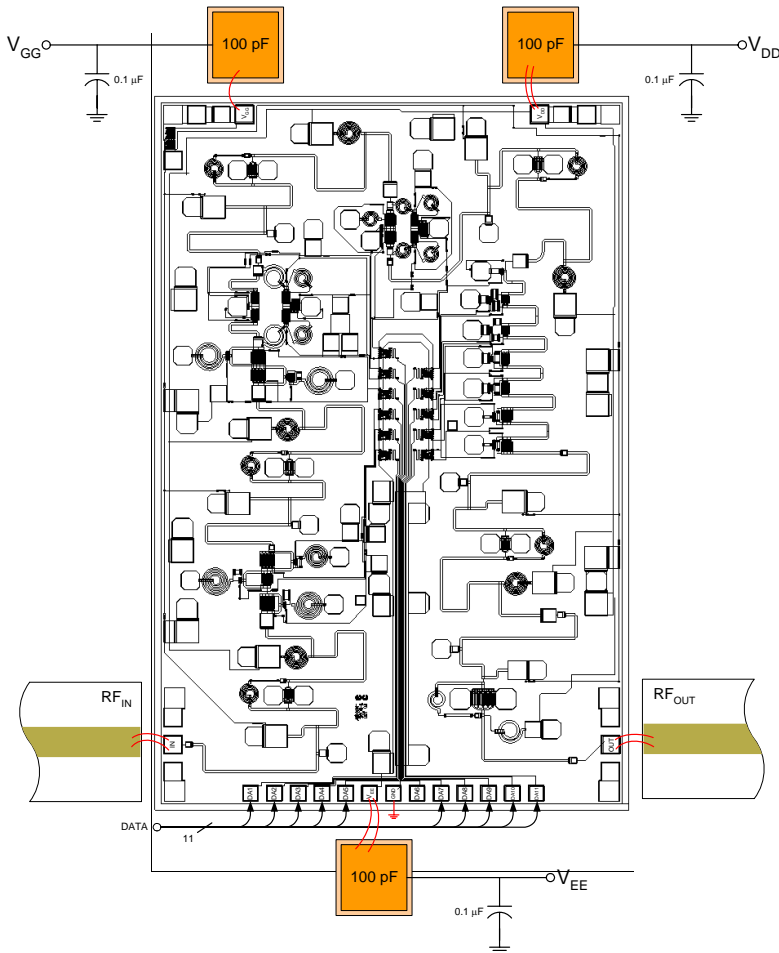
Chip Size: 5.978 x 3.975 x 0.075 mm (236 x 157 x 3 mils)



**Bond Pad Dimensions**

Pad	Size (µm)	Size (mils)
RF In and Out	150 x 150	6 x 6
DC Supply Voltages	150 x 150	6 x 6
DC Control Voltages	150 x 150	6 x 6

**Assembly and Bonding Diagram**



**Figure 5. Recommended bonding diagram.**  
Support circuitry typical of MMIC characterization fixture for CW testing.



**Assembly Instructions:**

**Die attach:** Use AuSn (80/20) 1-2 mil. preform solder. Limit time @ 300 °C to less than 5 minutes.

**Wirebonding:** Bond @ 160 °C using standard ball or thermal compression wedge bond techniques. For DC pad connections, use either ball or wedge bonds. For best RF performance, use wedge bonds of shortest length, although ball bonds are also acceptable.

**Biasing Note:** Must apply negative bias to V<sub>GG</sub> before applying positive bias to V<sub>DD</sub> to prevent damage to amplifier.